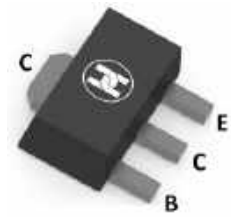
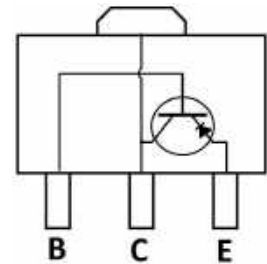


BIPOLAR TRANSISTOR (PNP)
FEATURES

- Complementary to D882
- Low Speed Switching
- Surface Mount device


SOT-89

MECHANICAL DATA

- Case: SOT-89
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.055 grams (approximate)

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current	I _C	-3	A
Collector Power Dissipation	P _C	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~+150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-base breakdown voltage	V _{(BR)CBO}	-40			V	I _C =-100uA, I _E =0
Collector-emitter breakdown voltage	V _{(BR)CEO}	-30			V	I _C =-10mA, I _B =0
Emitter-base breakdown voltage	V _{(BR)EBO}	-6			V	I _E =-100uA, I _C =0
Collector cut-off current	I _{CBO}			-1	uA	V _{CB} =-40V, I _E =0
Collector cut-off current	I _{CEO}			-10	uA	V _{CE} =-30V, I _B =0
Emitter cut-off current	I _{EBO}			-1	uA	V _{EB} =-6V, I _C =0
DC current gain	h _{FE}	60		400		V _{CE} =-2V, I _C =-1A
Collector-emitter saturation voltage	V _{CE(sat)}			-0.5	V	I _C =-2A, I _B =-0.2A
Base-emitter saturation voltage	V _{BE(sat)}			-1.5	V	I _C =-2A, I _B =-0.2A
Transition frequency	f _T	50			MHz	V _{CE} =-5V, I _C =-0.1A, f=10MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400
Marking	B772			